

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-20. (Canceled)

21. (Currently Amended) A personal computer comprising:

a semiconductor film provided over a substrate and comprising a source region, a drain region and a channel formation region provided between said source region and said drain region; [[and]]

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween; [[,]]

~~wherein lattices are continuously connected to each other at grain boundary of said semiconductor film according to high resolution TEM~~

a metal element for promoting crystallization, said metal element contained in said semiconductor film;

a layer comprising an element selected from the group consisting of titanium, tungsten, tantalum and molybdenum, said layer provided adjacent to at least one of said source region and said drain region with a silicide thereof therebetween;

an interlayer insulating film provided over said semiconductor film and said gate electrode; and

a contact hole provided in said interlayer insulating film and provided over said at least one of said source region and said drain region and provided over said layer comprising said element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

22. (Previously Presented) A computer according to claim 21 further comprising an auxiliary capacitance.

23. (Previously Presented) A computer according to claim 21 further comprising:
a pixel electrode;
an opposite electrode; and
a liquid crystal provided between said pixel electrode and said opposite electrode.

24. (Canceled)

25. (Currently Amended) A computer according to claim 21 wherein a channel length of said channel formation region is 2 μm or shorter.

26. (New) A computer according to claim 21 wherein said metal element is selected from the group consisting of nickel, cobalt, iron, tin, lead, palladium, platinum, copper and gold.

27. (New) computer according to claim 21 further comprising a source wiring line provided over said layer comprising said element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

28. (New) A computer according to claim 21 further comprising a drain wiring line provided over said layer comprising said element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

29. (New) A computer according to claim 21 wherein said semiconductor film comprises silicon.

30. (New) A personal computer comprising:

a semiconductor film provided over a substrate and comprising a source region, a drain region and a channel formation region provided between said source region and said drain region;

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween;

a metal element for promoting crystallization, said metal element contained in said semiconductor film;

a layer comprising an element selected from the group consisting of titanium, tungsten, tantalum and molybdenum, said layer provided adjacent to at least one of said source region and said drain region with a silicide thereof therebetween;

an interlayer insulating film comprising silicon oxide provided over said semiconductor film and said gate electrode; and

a contact hole provided in said interlayer insulating film and provided over said at least one of said source region and said drain region and provided over said layer comprising said element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

31. (New) A computer according to claim 30 further comprising an auxiliary capacitance.

32. (New) A computer according to claim 30 further comprising:

a pixel electrode;

an opposite electrode; and

a liquid crystal provided between said pixel electrode and said opposite electrode.

33. (New) A computer according to claim 30 wherein a channel length of said channel formation region is 2 μm or shorter.

34. (New) A computer according to claim 30 wherein said metal element is selected from the group consisting of nickel, cobalt, iron, tin, lead, palladium, platinum, copper and gold.

35. (New) A computer according to claim 30 wherein said semiconductor film comprises silicon.

36. (New) A personal computer comprising:

a semiconductor film provided over a substrate and comprising a source region, a drain region and a channel formation region provided between said source region and said drain region;

a gate electrode provided adjacent to said channel formation region with a gate insulating film therebetween;

a metal element for promoting crystallization, said metal element contained in said semiconductor film;

an island pattern comprising an element selected from the group consisting of titanium, tungsten, tantalum and molybdenum, said island pattern provided adjacent to at least one of said source region and said drain region with a silicide thereof therebetween;

an interlayer insulating film provided over said semiconductor film and said gate electrode; and

a contact hole provided in said interlayer insulating film and provided over said at least one of said source region and said drain region and provided over said island pattern comprising said element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

37. (New) A computer according to claim 36 further comprising an auxiliary capacitance.

38. (New) A computer according to claim 36 further comprising:

a pixel electrode;

an opposite electrode; and

a liquid crystal provided between said pixel electrode and said opposite electrode.

39. (New) A computer according to claim 36 wherein a channel length of said channel formation region is 2 μm or shorter.

40. (New) A computer according to claim 36 wherein said metal element is selected from the group consisting of nickel, cobalt, iron, tin, lead, palladium, platinum, copper and gold.

41. (New) A computer according to claim 36 wherein said semiconductor film comprises silicon.